

<u>1000V 15A</u> APT15DQ100K APT15DQ100KG*

*G Denotes RoHS Compliant, Pb Free Terminal Finish.

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

PRODUCT APPLICATIONS

- Anti-Parallel Diode
 -Switchmode Power Supply
 -Inverters
- Free Wheeling Diode
 -Motor Controllers
 -Converters
 -Inverters
- Snubber Diode

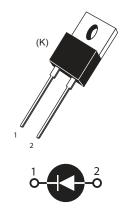
• PFC

PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular TO-220 Package
- Low Forward Voltage
- Low Leakage Current
- Avalanche Energy Rated

PRODUCT BENEFITS

- Low Losses
- · Low Noise Switching
- Cooler Operation
- Higher Reliability Systems
- Increased System Power Density



1 - Cathode 2 - Anode

All Ratings: $T_{o} = 25^{\circ}C$ unless otherwise specified.

MAXIMUM RATINGS

Symbol	Characteristic / Test Conditions	APT15DQ100K(G)	UNIT			
V _R	Maximum D.C. Reverse Voltage					
V _{RRM}	Maximum Peak Repetitive Reverse Voltage	1000	Volts			
V _{RWM}	Maximum Working Peak Reverse Voltage					
I _{F(AV)}	Maximum Average Forward Current (T _C = 126°C, Duty Cycle = 0.5)	15				
I _{F(RMS)}	RMS Forward Current (Square wave, 50% duty)	29	Amps			
I _{FSM}	Non-Repetitive Forward Surge Current $(T_J = 45^{\circ}C, 8.3ms)$	80				
E _{AVL}	Avalanche Energy (1A, 40mH)	20	mJ			
T_,T _{STG}	Operating and StorageTemperature Range	-55 to 175				
Τ _L	Lead Temperature for 10 Sec.	300	− °C			

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	ТҮР	МАХ	UNIT
V _F	Forward Voltage	I _F = 15A		2.5	3.0	Volts
		I _F = 30A		3.06		
		I _F = 15A, T _J = 125°C		1.92		
I _{RM}	Maximum Reverse Leakage Current	V _R = 1000V			100	- μΑ
		V _R = 1000V, T _J = 125°C			500	
C _T	Junction Capacitance, $V_R = 200V$			12		pF

Back of Case - Cathode

DYNAMIC CHARACTERISTICS

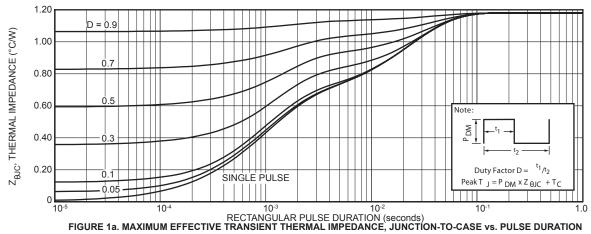
APT15DQ100K(G)

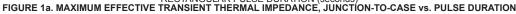
Symbol	Characteristic	Test Conditions	MIN	ТҮР	MAX	UNIT
t _{rr}	Reverse Recovery Time $I_F = 1A, di_F/dt =$	covery Time $I_F = 1A$, $di_F/dt = -100A/\mu s$, $V_R = 30V$, $T_J = 25^{\circ}C$		20		ns
t _{rr}	Reverse Recovery Time	I _F = 15A, di _F /dt = -200A/μs V _R = 667V, T _C = 25°C	-	235		115
Q _{rr}	Reverse Recovery Charge		-	185		nC
I _{RRM}	Maximum Reverse Recovery Current		-	3	-	Amps
t _{rr}	Reverse Recovery Time	I _F = 15A, di _F /dt = -200A/μs V _R = 667V, T _C = 125°C	-	300		ns
Q _{rr}	Reverse Recovery Charge		-	810		nC
I _{RRM}	Maximum Reverse Recovery Current		-	6	-	Amps
t _{rr}	Reverse Recovery Time	I _F = 15A, di _F /dt = -1000A/μs V _R = 667V, T _C = 125°C	-	125		ns
Q _{rr}	Reverse Recovery Charge		-	1150		nC
I _{RRM}	Maximum Reverse Recovery Current		-	19		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	ТҮР	MAX	UNIT
R _{θJC}	Junction-to-Case Thermal Resistance			1.18	°C/W
W _T	Package Weight		0.07		οz
			1.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

Microsemi reserves the right to change, without notice, the specifications and information contained herein.





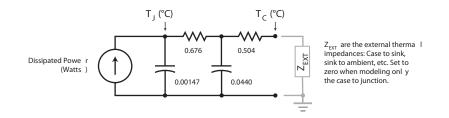
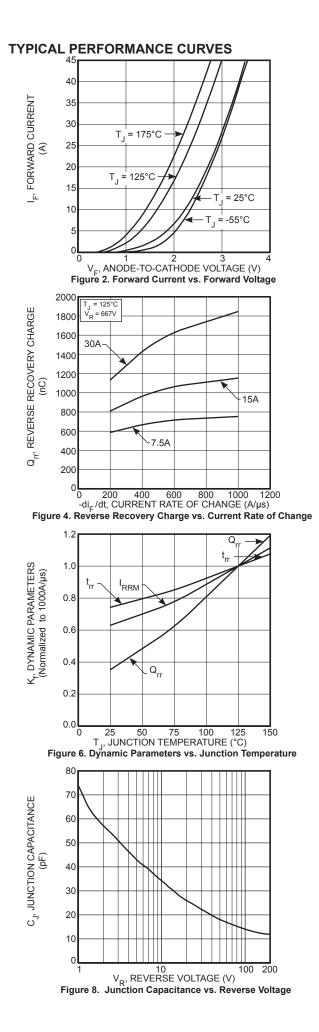


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL



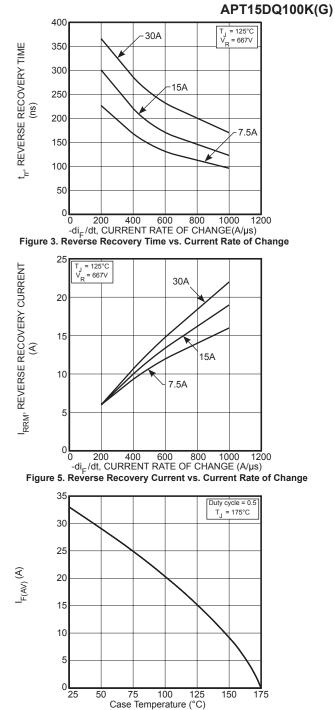
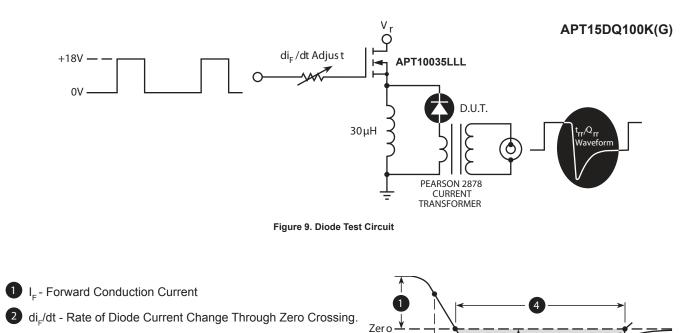
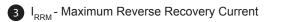


Figure 7. Maximum Average Forward Current vs. CaseTemperature





t_{rr} - Reverse Recovery Time measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and 0.25, I_{RRM} passes through zero.

5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{RR} .

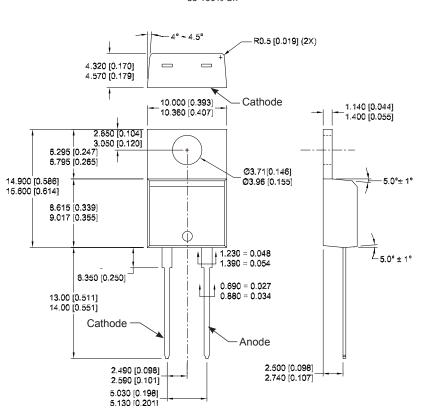


5

3

←2

0.25 I_{RRM}





Disclaimer:

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customer's final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/terms-a-conditions.